

NTST30100SG, NTSB30100S-1G

Very Low Forward Voltage Trench-based Schottky Rectifier

Exceptionally Low $V_F = 0.39\text{ V}$ at $I_F = 5\text{ A}$

Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- These are Pb-Free Devices

Typical Applications

- Switching Power Supplies including Notebook/Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing Diodes
- Reverse Battery Protection
- Instrumentation

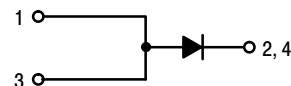
Mechanical Characteristics

- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in
- Weight (Approximately): 1.9 Grams
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec

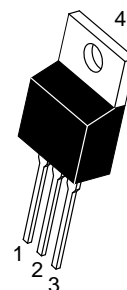


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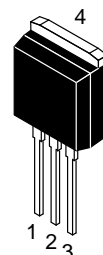
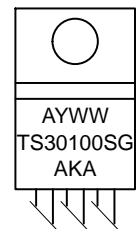
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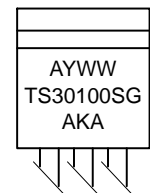
MARKING DIAGRAMS



TO-220
CASE 221A
STYLE 6



i²PAK (TO-262)
CASE 418D
STYLE 3



A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package
AKA = Polarity Designator

ORDERING INFORMATION

| Device | Package | Shipping† |
|---------------|---------------------|---------------|
| NTST30100SG | TO-220 (Pb-Free) | 50 Units/Rail |
| NTSB30100S-1G | TO-262 (Pb-Free) | 50 Units/Rail |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--|---------------------------------|-------------|------------------|
| Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage | V_{RRM} V_{RWM} V_R | 100 | V |
| Average Rectified Forward Current (Rated V_R , $T_C = 105^\circ\text{C}$) | $I_{F(AV)}$ | 30 | A |
| Peak Repetitive Forward Current (Rated V_R , Square Wave, 20 kHz, $T_C = 95^\circ\text{C}$) | I_{FRM} | 60 | A |
| Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz) | I_{FSM} | 250 | A |
| Operating Junction Temperature | T_J | -40 to +150 | $^\circ\text{C}$ |
| Storage Temperature | T_{stg} | -65 to +175 | $^\circ\text{C}$ |
| Voltage Rate of Change (Rated V_R) | dv/dt | 10,000 | V/ μs |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

| Rating | Symbol | Value | Unit |
|---|------------------------------------|-----------|--------------------|
| Maximum Thermal Resistance Junction-to-Case Junction-to-Ambient | $R_{\theta JC}$ $R_{\theta JA}$ | 2.0 70 | $^\circ\text{C/W}$ |

ELECTRICAL CHARACTERISTICS

| Rating | Symbol | Typ | Max | Unit |
|---|--------|---|--------------------------------------|--|
| Maximum Instantaneous Forward Voltage (Note 1) ($I_F = 5\text{ A}$, $T_J = 25^\circ\text{C}$) ($I_F = 10\text{ A}$, $T_J = 25^\circ\text{C}$) ($I_F = 30\text{ A}$, $T_J = 25^\circ\text{C}$) ($I_F = 5\text{ A}$, $T_J = 125^\circ\text{C}$) ($I_F = 10\text{ A}$, $T_J = 125^\circ\text{C}$) ($I_F = 30\text{ A}$, $T_J = 125^\circ\text{C}$) | V_F | 0.47 0.55 0.84 0.39 0.51 0.7 | - - 0.95 - - 0.78 | V |
| Maximum Instantaneous Reverse Current (Note 1) ($V_R = 70\text{ V}$, $T_J = 25^\circ\text{C}$) ($V_R = 70\text{ V}$, $T_J = 125^\circ\text{C}$) (Rated dc Voltage, $T_J = 25^\circ\text{C}$) (Rated dc Voltage, $T_J = 125^\circ\text{C}$) | I_R | 27 11 70 23 | 1000 45 | μA mA μA mA |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$

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TYPICAL CHARACTERISTICS

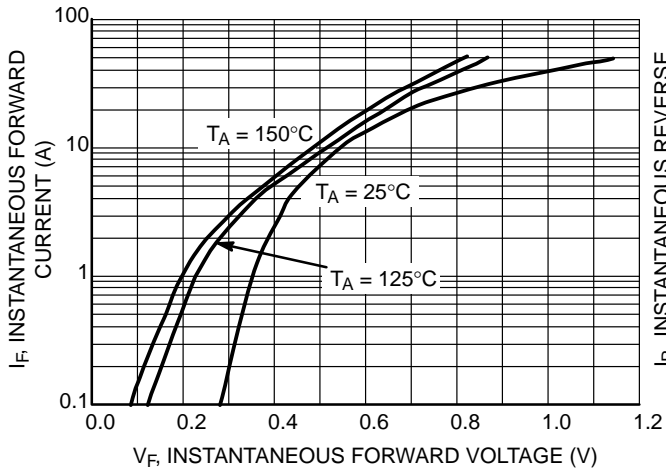


Figure 1. Typical Instantaneous Forward Characteristics

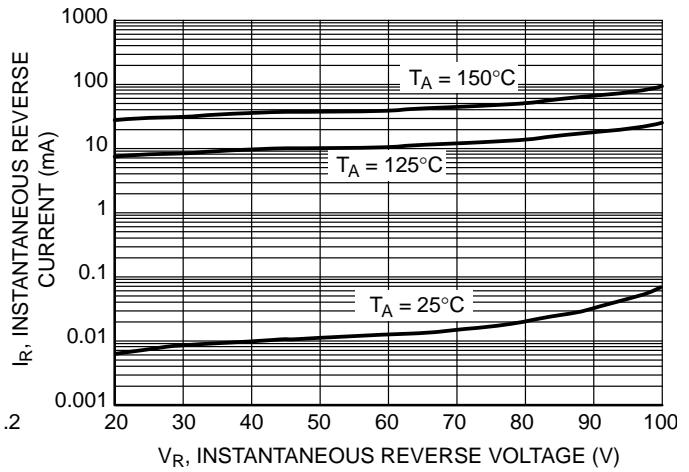


Figure 2. Typical Reverse Characteristics

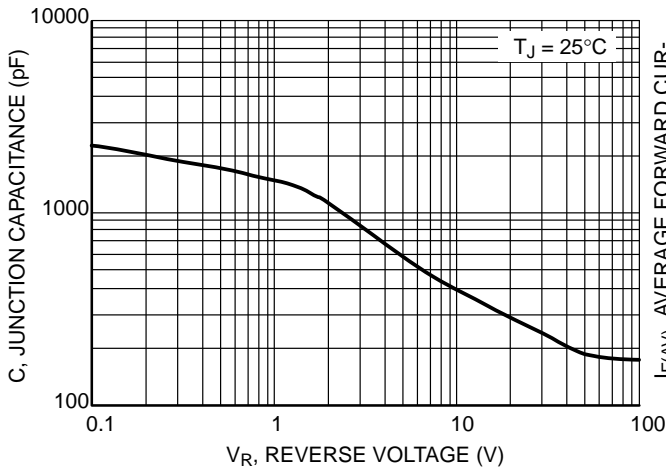


Figure 3. Typical Junction Capacitance

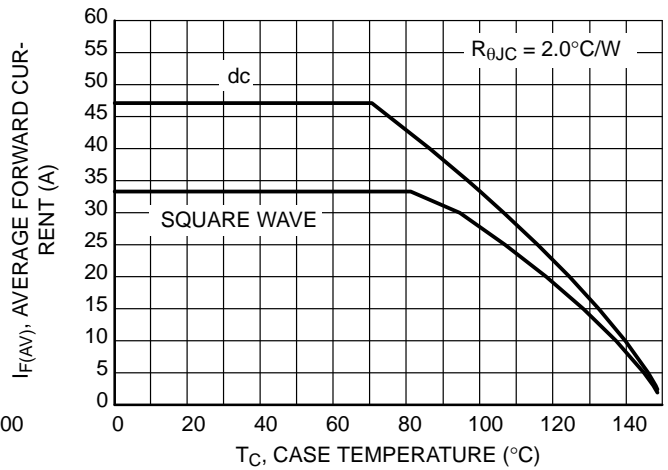


Figure 4. Current Derating, Case

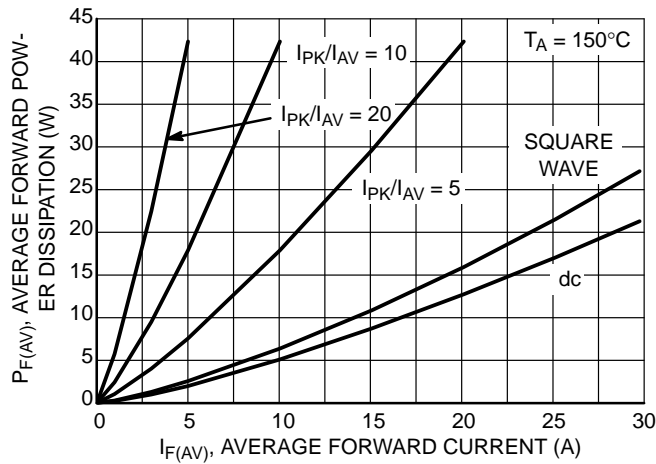


Figure 5. Forward Power Dissipation

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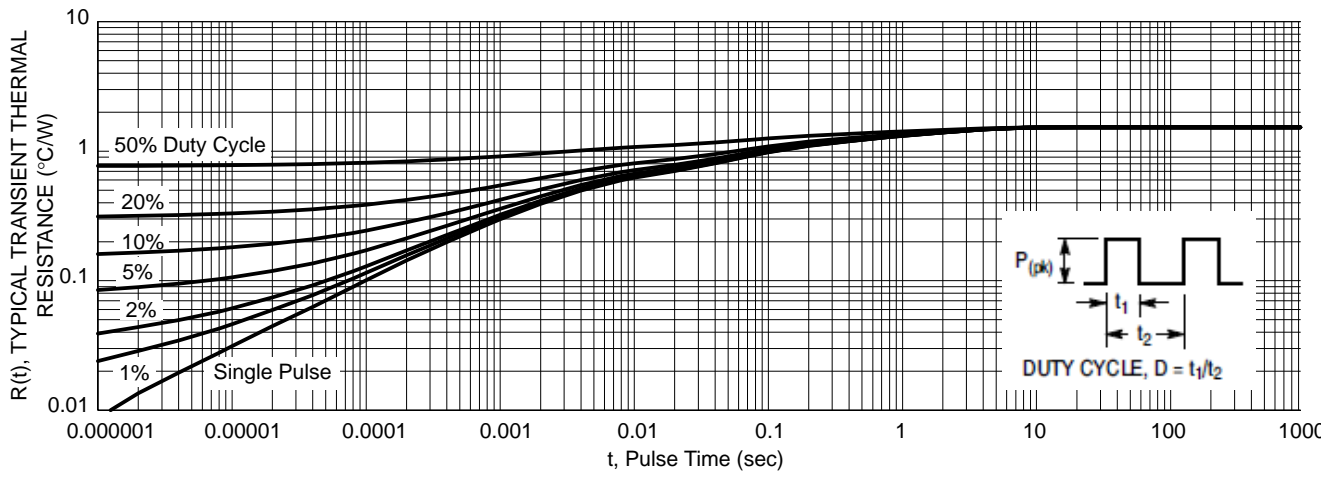
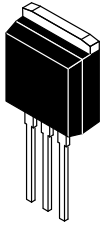


Figure 6. Typical Transient Thermal Response, Junction-to-Case

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

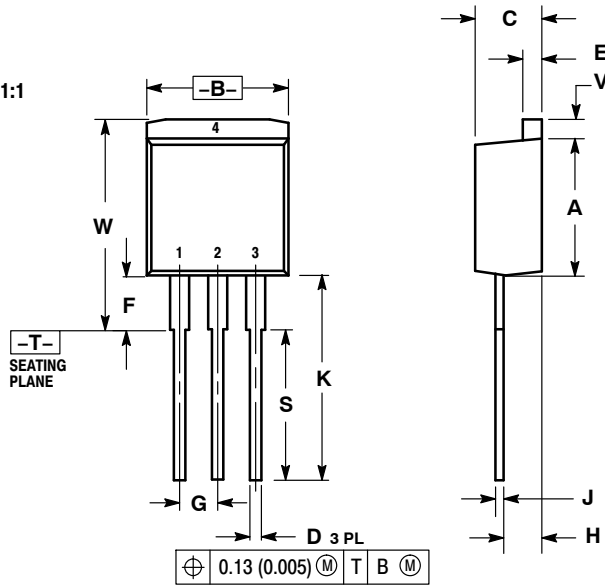
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SCALE 1:1

I²PAK (TO-262)
CASE 418D-01
ISSUE D

DATE 16 OCT 2007



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

| DIM | INCHES | | MILLIMETERS | |
|-----|-----------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.335 | 0.380 | 8.51 | 9.65 |
| B | 0.380 | 0.406 | 9.65 | 10.31 |
| C | 0.160 | 0.185 | 4.06 | 4.70 |
| D | 0.026 | 0.035 | 0.66 | 0.89 |
| E | 0.045 | 0.055 | 1.14 | 1.40 |
| F | 0.122 REF | | 3.10 REF | |
| G | 0.100 BSC | | 2.54 BSC | |
| H | 0.094 | 0.110 | 2.39 | 2.79 |
| J | 0.013 | 0.025 | 0.33 | 0.64 |
| K | 0.500 | 0.562 | 12.70 | 14.27 |
| S | 0.390 REF | | 9.90 REF | |
| V | 0.045 | 0.070 | 1.14 | 1.78 |
| W | 0.522 | 0.551 | 13.25 | 14.00 |

STYLE 1:

- PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:

- PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 3:

- PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 4:

- PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

| | | |
|-------------------------|----------------------------------|---|
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